Atlas DCA

semiconductor component analyser

Model: DCA55

PRODUCT BRIEF

Features

• Connect any way round.

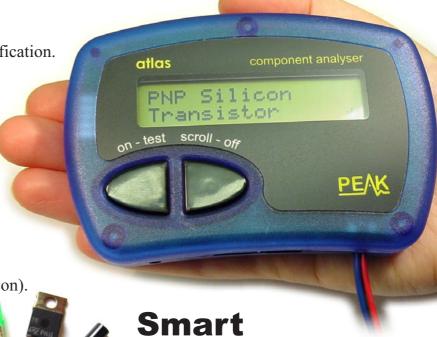
• Automatic component type identification.

- Automatic pinout identification.
- Transistor gain measurement.
- MOSFET gate threshold measurement.
- PN iunction characteristics measurements.
- Leakage current measurement.
- Auto power on and power off.
- Ultra-slim and compact design.

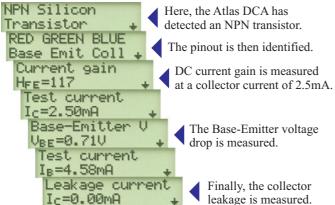
Supported Parts

• Transistors (Germanium and Silicon).

- Darlingtons.
- MOSFETs.
- Junction FETs.
- Low power thyristors and triacs.
- LEDs (including bicolour types).
- Diodes and diode networks.



Example Display for a typical transistor:





Technical Specifications

Parameter	Minimum	Typical	Maximum	Notes
Peak test current into S/C	-5.5mA	J1	5.5mA	1
Peak test voltage across O/C	-5.1V		5.1V	1
Measurable transistor gain range (H _{FE})	4		65000	2
Transistor gain accuracy	-3%-5 HFE		+3%+5 HFE	2,9
Transistor V _{CEO}	2.0V		3.0V	2
Transistor V _{BE} accuracy	-2%-20mV		+2%+20mV	9
V _{BE} for Darlington identification		1.0V		3
V _{BE} for Darlington identification (shunted)		0.8V		4
Acceptable transistor V _{BE}			1.80V	
Base-emitter shunt resistance threshold		60kΩ		
Transistor collector-emitter test current	2.45mA	2.50mA	2.55mA	
Acceptable transistor collector leakage		0.7mA		6
MOSFET gate threshold range	0.1V		5.0V	5
MOSFET gate threshold accuracy	-2%-20mV		+2%+20mV	5
MOSFET drain-source test current	2.45mA	2.50mA	2.55mA	
MOSFET minimum gate resistance		8kΩ		
Thyristor/Triac gate test current		4.5mA		7
Thyristor/Triac load test current		5.0mA		
Diode test current			5.0mA	
Diode forward voltage accuracy	-2%-20mV		+2%+20mV	
V _F for LED identification		1.50V		
Battery type	GP23A 12V Alkaline			
Battery voltage range	7.50V	12V		
Battery voltage warning threshold		8.25V		
Inactivity power-down period		30 secs		
Dimensions (excluding test leads)	103 x 70 x 20 mm			
Operating temperature range	0°C		50°C	8

Convenient

- Between any pair of test clips. Collector current of 2.50mÅ.
- Resistance across reverse biased base-emitter $> 60 k \ \Omega.$
- Resistance across reverse biased base-emitter \leq 60k $\Omega.$ Drain-source current of 2.50mA.

Accurate

- Collector-emitter voltage of 5.0V.
 Thyristor quadrant I, Triac quadrants I and III.
 Subject to acceptable LCD visibility.
- 9. BJT with no shunt resistors

11/05

Peak Electronic Design Limited

Atlas House, Harpur Hill Business Park, Buxton, Derbyshire, SK17 9JL. Tel.+44 (0)1298 70012, Fax. +44 (0)1298 70046